BUK9609-75A

N-channel TrenchMOS logic level FET

Rev. 03 — 22 September 2008 **Product data sheet**

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

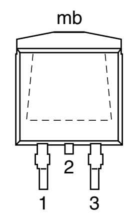
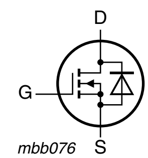
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	75	V
I_D	drain current	$V_{GS} = 5$ V; $T_j = 25$ °C; see Figure 3; see Figure 1	-	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	-	230	W
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75$ A; $V_{sup} \leq 75$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped	-	-	562	mJ
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5$ V; $I_D = 25$ A; $T_j = 25$ °C	-	-	9.95	mΩ
		$V_{GS} = 5$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 12; see Figure 15	-	7.6	9	mΩ

founded by Philips

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT404 (D2PAK)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

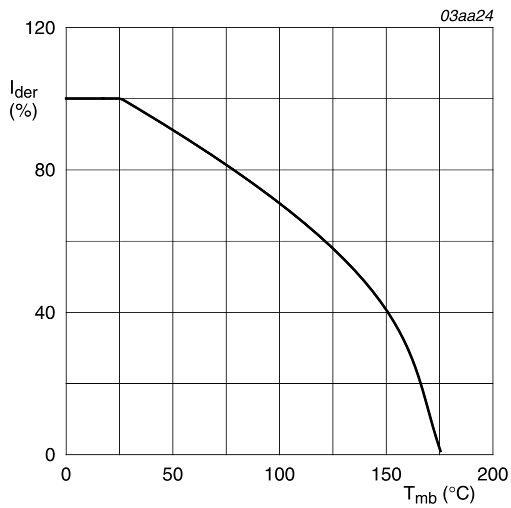
Type number	Package		
	Name	Description	Version
BUK9609-75A	D2PAK	Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

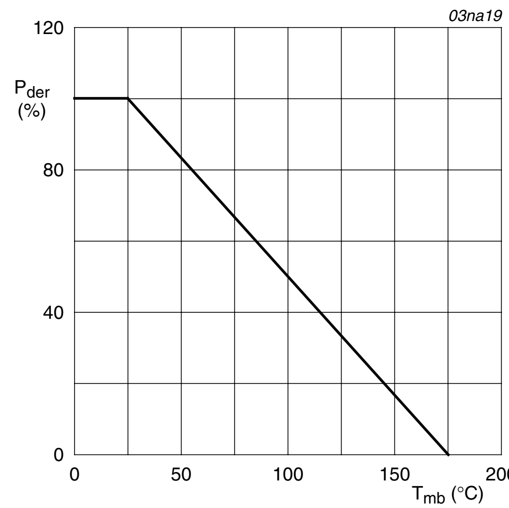
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	75	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ	-	75	V
V_{GS}	gate-source voltage		-10	10	V
I_D	drain current	$V_{GS} = 5$ V; $T_j = 100$ °C; see Figure 1	-	65	A
		$V_{GS} = 5$ V; $T_j = 25$ °C; see Figure 3; see Figure 1	-	75	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; $t_p \leq 10$ µs; pulsed; see Figure 3	-	440	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2	-	230	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
V_{GSM}	peak gate-source voltage	pulsed; $t_p \leq 50$ µs	-15	15	V
Source-drain diode					
I_S	source current	$T_{mb} = 25$ °C	-	75	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; $T_{mb} = 25$ °C	-	440	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75$ A; $V_{sup} \leq 75$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped	-	562	mJ



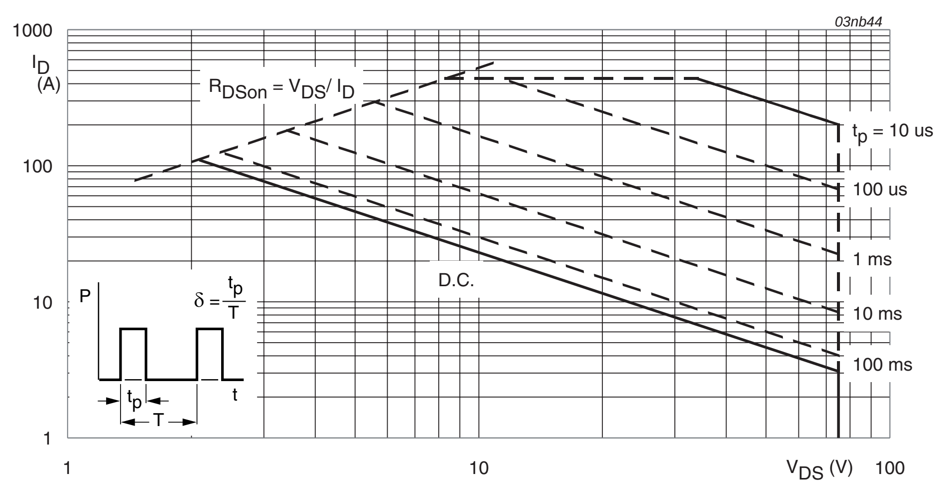
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C$; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

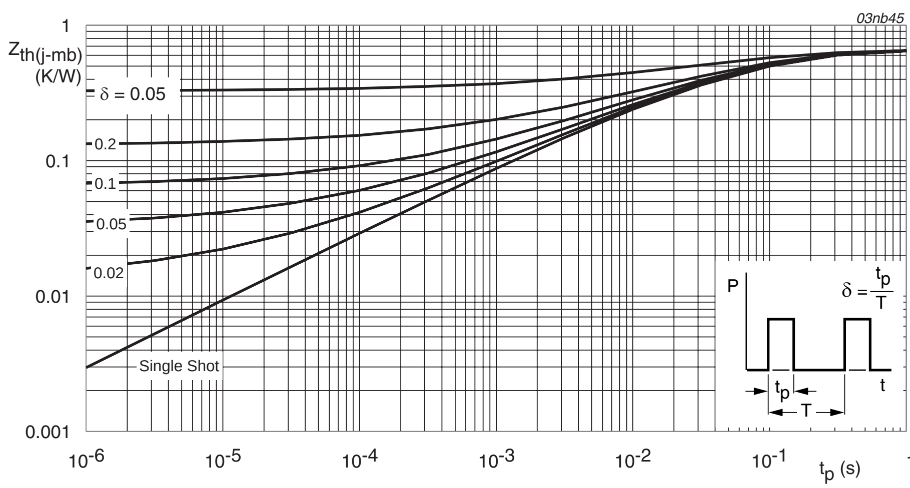
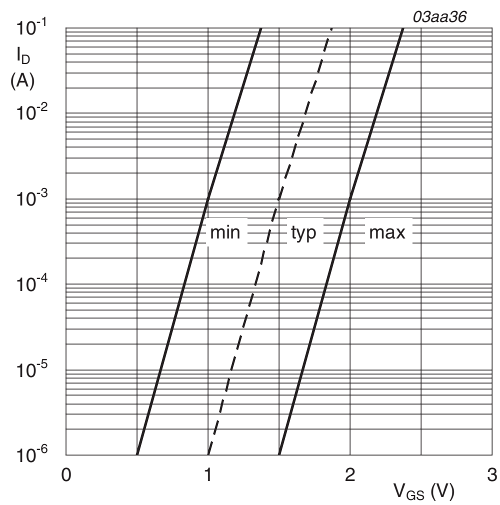


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

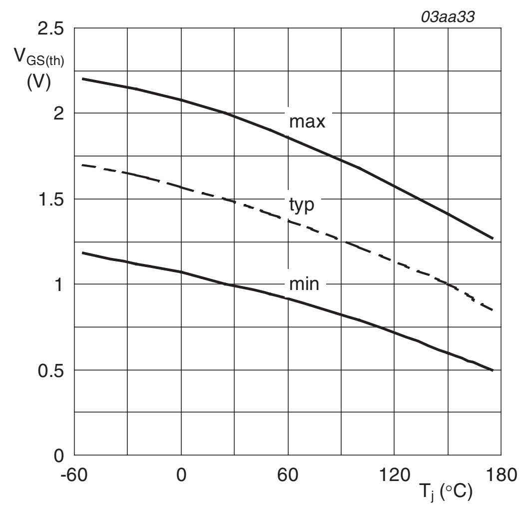
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	75	-	-	V
		I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 6	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 6	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 6	-	-	2.3	V
I_{DSS}	drain leakage current	V_{DS} = 75 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
		V_{DS} = 75 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	µA
I_{GSS}	gate leakage current	V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 °C	-	2	100	nA
		V_{DS} = 0 V; V_{GS} = -10 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C	-	-	9.95	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 175 °C; see Figure 12; see Figure 15	-	-	18.9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C	-	7.23	8.5	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 25 °C; see Figure 12; see Figure 15	-	7.6	9	mΩ
Dynamic characteristics						
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 14	-	6631	8840	pF
C_{oss}	output capacitance		-	905	1090	pF
C_{rss}	reverse transfer capacitance		-	610	840	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 10 Ω; T_j = 25 °C	-	47	-	ns
t_r	rise time		-	185	-	ns
$t_{d(off)}$	turn-off delay time		-	424	-	ns
t_f	fall time		-	226	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to centre of die; T_j = 25 °C	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T_j = 25 °C	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bond pad; T_j = 25 °C	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 13	-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	70.3	-	ns
Q_r	recovered charge		-	213	-	nC



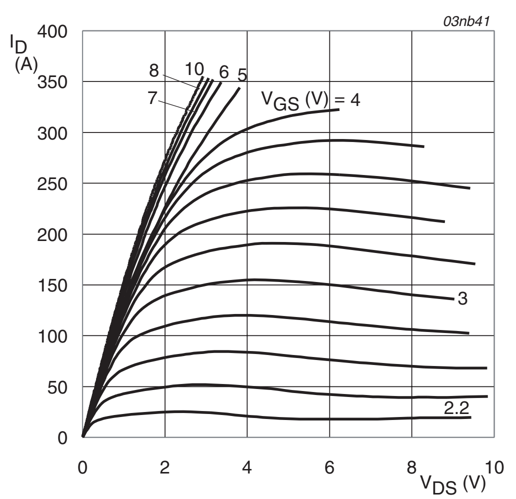
$T_j = 25\,°C; V_{DS} = V_{GS}$

Fig 5. Sub-threshold drain current as a function of gate-source voltage



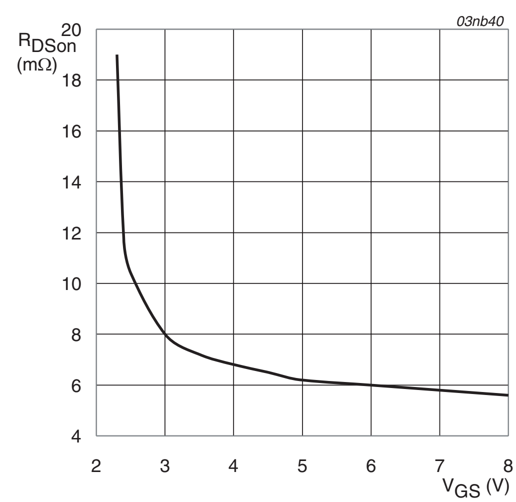
$I_D = 1\,mA; V_{DS} = V_{GS}$

Fig 6. Gate-source threshold voltage as a function of junction temperature



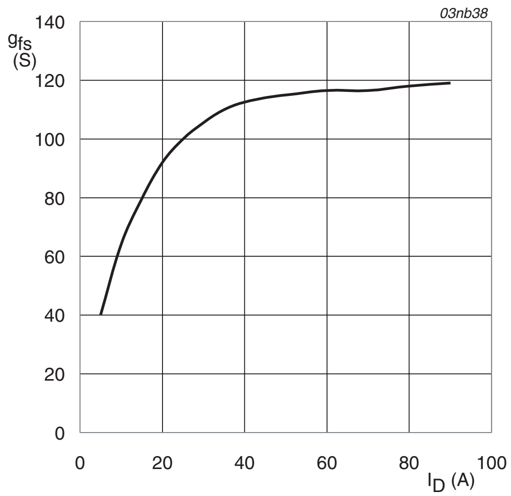
$T_j = 25°C; t_p = 300\mu s$

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



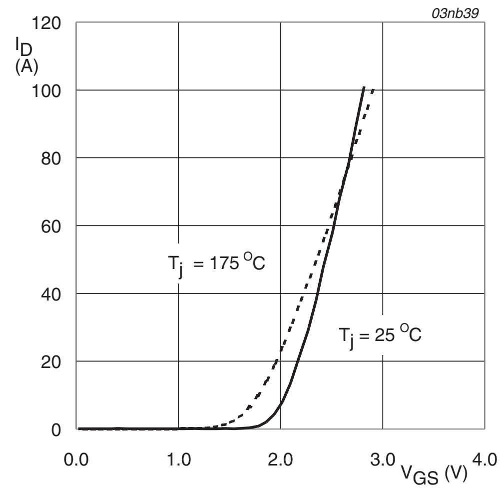
$T_j = 25°C; I_D = 25A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



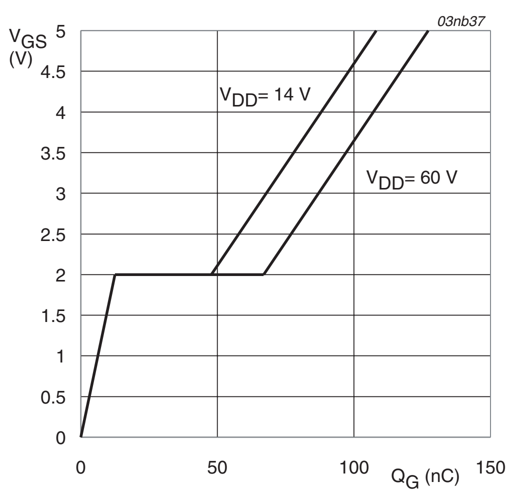
$T_j = 25°C; V_{DS} = 25V$

Fig 9. Forward transconductance as a function of drain current; typical values



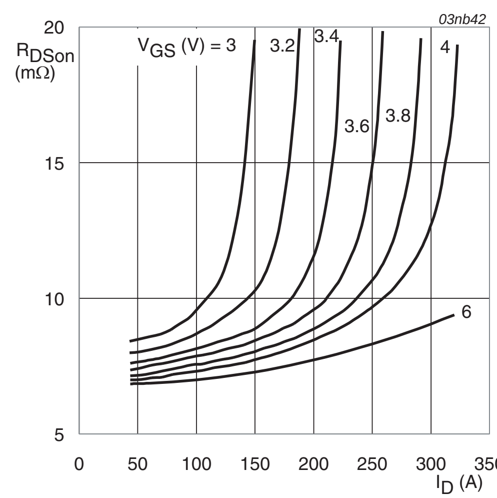
$V_{DS} = 25V$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



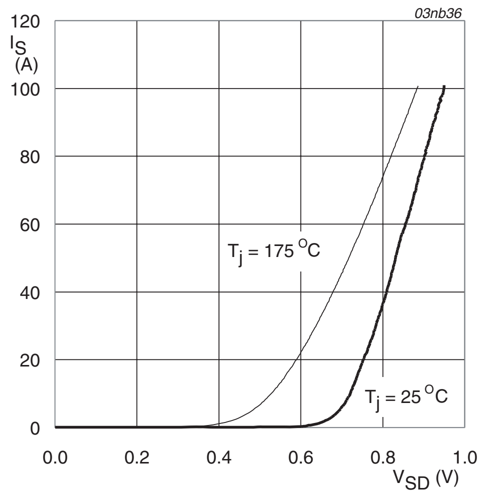
$T_j = 25°C; I_D = 25A$

Fig 11. Gate-source voltage as a function of gate charge; typical values



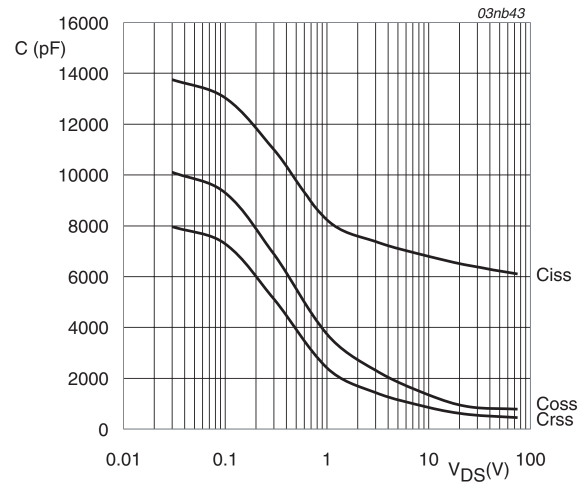
$T_j = 25°C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



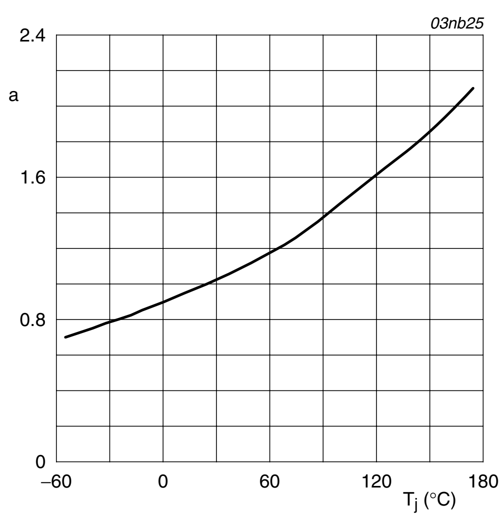
$$V_{GS} = 0V$$

Fig 13. Reverse diode current as a function of reverse diode voltage; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

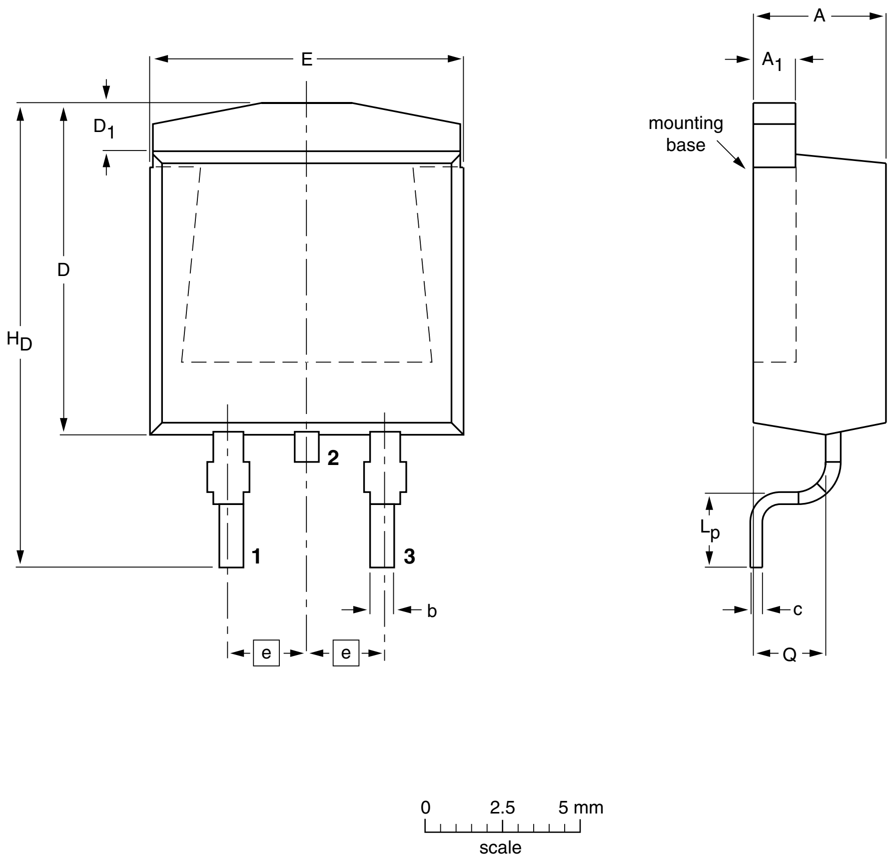


$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 15. Normalized drain-source on-state resistance factor as a function of junction temperature

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 16. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9509-75A_3	20080922	Product data sheet	-	BUK9509_9609_75A-02
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number BUK9609-75A separated from data sheet BUK9509_9609_75A-02.			
BUK9509_9609_75A-02	20001106	Product data sheet	-	BUK9509_9609_75A-01
BUK9509_9609_75A-01	20001010	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

9.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

TrenchMOS — is a trademark of NXP B.V.

10. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

11. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: Rev. 03 — 22 September 2008
Document identifier: BUK9609-75A_3